

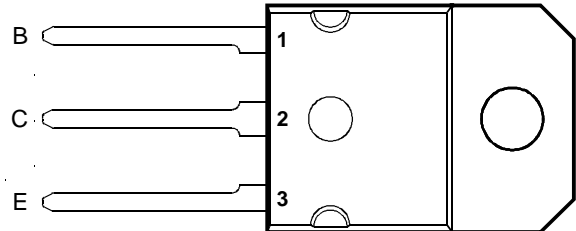
# TIP160, TIP161, TIP162 NPN SILICON POWER DARLINGTONS

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JUNE 1973 - REVISED MARCH 1997

- 50 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- 15 A Peak Collector Current
- Maximum  $V_{CE(sat)}$  of 2.8 V at  $I_C = 6.5$  A
- $I_{CEX(sus)}$  7 A at rated  $V_{(BR)CEO}$

SOT-93 PACKAGE  
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRAA

## absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	TIP160	$V_{CBO}$	320	V
	TIP161		350	
	TIP162		380	
Collector-emitter voltage ( $I_B = 0$ )	TIP160	$V_{CEO}$	320	V
	TIP161		350	
	TIP162		380	
Emitter-base voltage		$V_{EBO}$	5	V
Continuous collector current		$I_C$	10	A
Peak collector current (see Note 1)		$I_{CM}$	15	A
Peak commutating anti-parallel diode current ( $I_B = 0$ ) (see Note 2)		$I_{EM}$	10	A
Continuous base current		$I_B$	1	A
Continuous device dissipation at (or below) 100°C case temperature (see Note 3)		$P_{tot}$	50	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 4)		$P_{tot}$	3	W
Operating junction temperature range		$T_j$	-65 to +150	°C
Storage temperature range		$T_{stg}$	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		$T_L$	260	°C

- NOTES: 1. This value applies for  $t_p \leq 10$  ms, duty cycle  $\leq 10\%$ .  
 2. This value applies to the total collector-terminal current when the collector is at negative potential with respect to the emitter.  
 3. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.  
 4. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.

## PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.

# TIP160, TIP161, TIP162

## NPN SILICON POWER DARLINGTONS

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### electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$I_{CEO}$	Collector-emitter cut-off current	$V_{CE} = 320\text{ V}$	$I_B = 0$	TIP160				
		$V_{CE} = 350\text{ V}$	$I_B = 0$	TIP161			1	mA
		$V_{CE} = 380\text{ V}$	$I_B = 0$	TIP162				
$I_{CEX(sus)}$	Collector-emitter sustaining current	$V_{CLAMP} = V_{(BR)CEO}$			7			A
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 5\text{ V}$	$I_C = 0$			100	mA	
$h_{FE}$	Forward current transfer ratio	$V_{CE} = 2.2\text{ V}$	$I_C = 4\text{ A}$	(see Notes 5 and 6)	200			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = 0.1\text{ A}$	$I_C = 6.5\text{ A}$	(see Notes 5 and 6)			2.8	V
		$I_B = 1\text{ A}$	$I_C = 10\text{ A}$				2.9	
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_B = 0.1\text{ A}$	$I_C = 6.5\text{ A}$	(see Notes 5 and 6)			2.2	V
$V_{EC}$	Parallel diode forward voltage	$I_E = 10\text{ A}$	$I_B = 0$	(see Notes 5 and 6)			3.5	V

NOTES: 5. These parameters must be measured using pulse techniques,  $t_p = 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

### thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			41.7	°C/W
$C_{\theta C}$	Thermal capacitance of case		1.4		J/°C

### resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
$t_d$	Delay time	$I_C = 6.5\text{ A}$ $V_{BE(off)} = -5\text{ V}$	$I_{B(on)} = 100\text{ mA}$ $R_L = 5\text{ }\Omega$	$I_{B(off)} = -100\text{ mA}$		40		ns
$t_r$	Rise time					1.5		$\mu\text{s}$
$t_s$	Storage time					2.2		$\mu\text{s}$
$t_f$	Fall time					2.6		$\mu\text{s}$

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PARAMETER MEASUREMENT INFORMATION

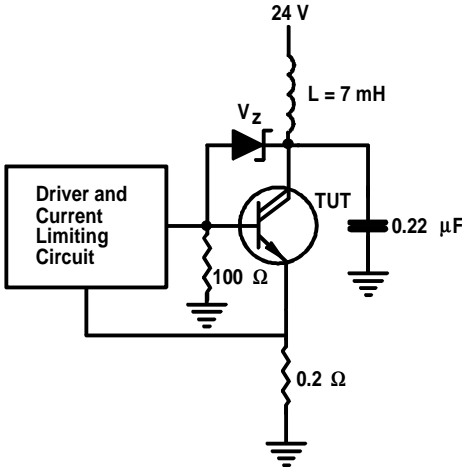


Figure 1. Functional Test Circuit

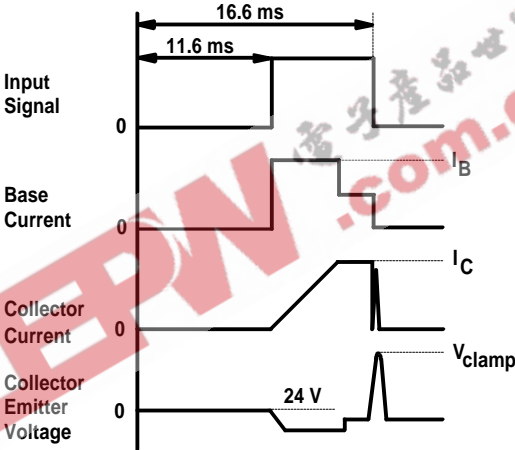


Figure 2. Functional Test Waveforms

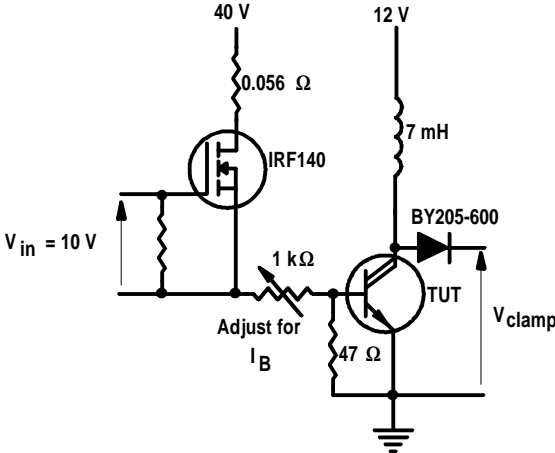


Figure 3. Switching Test Circuit

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## TYPICAL CHARACTERISTICS

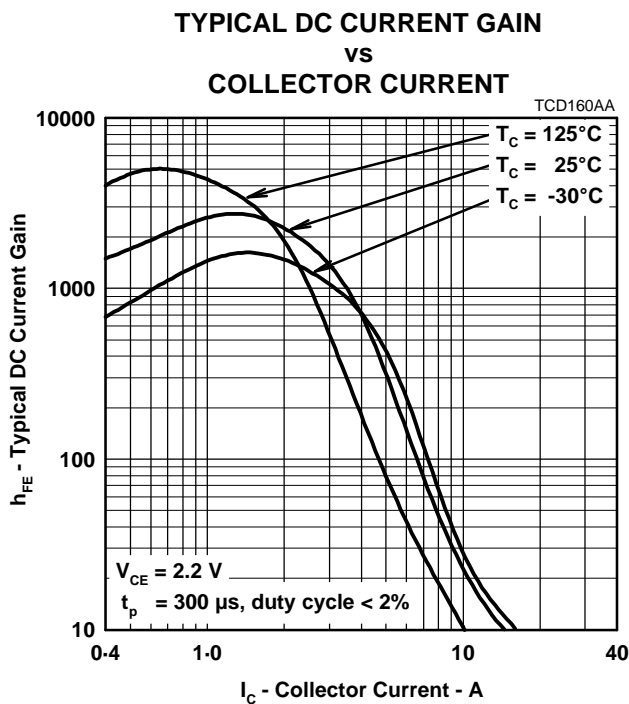


Figure 4.

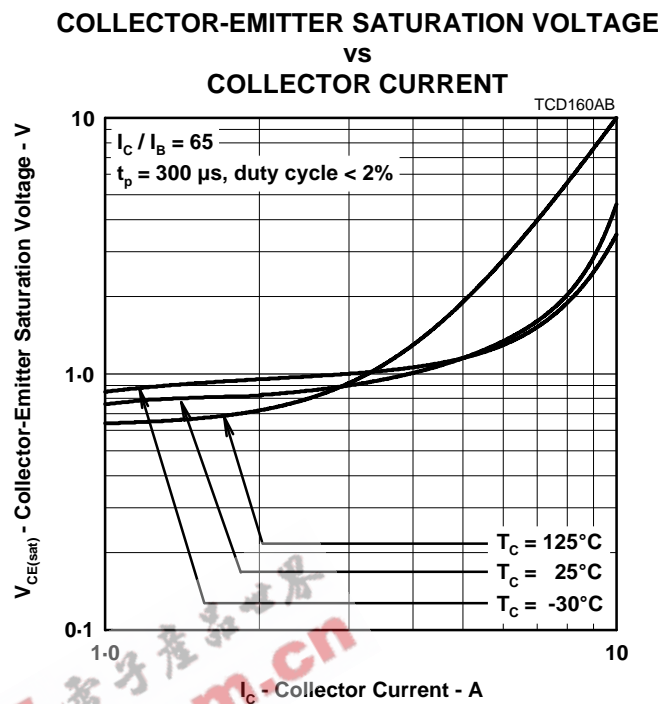


Figure 5.

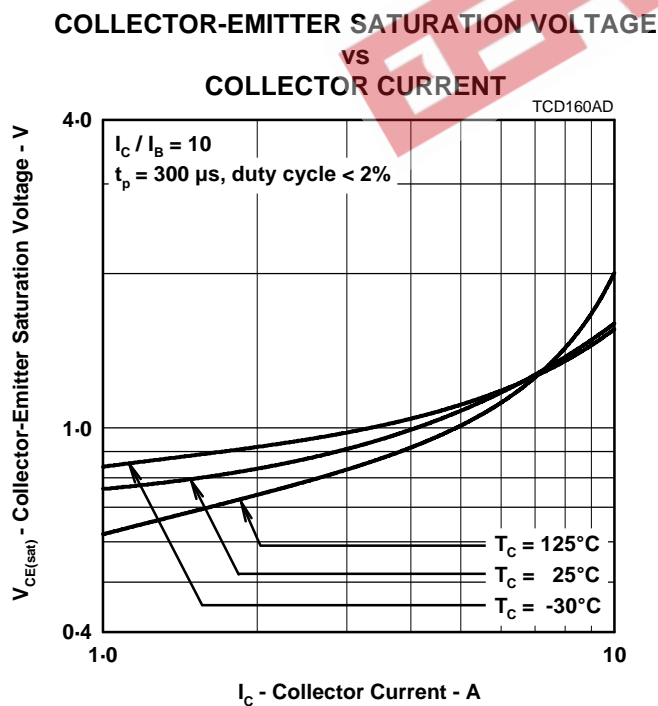


Figure 6.

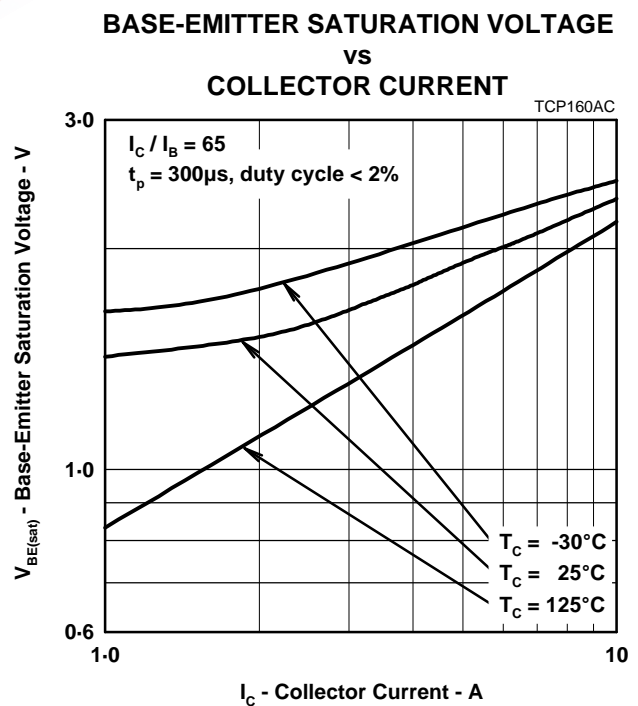


Figure 7.

## PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

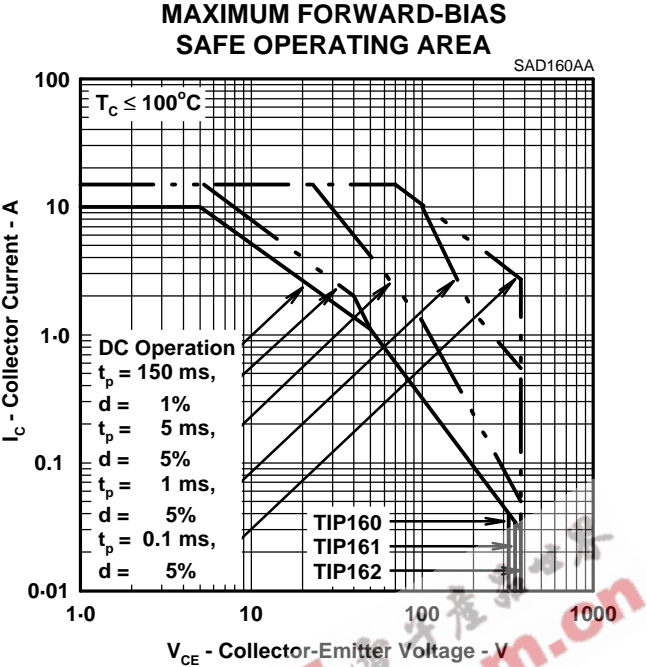


Figure 8.

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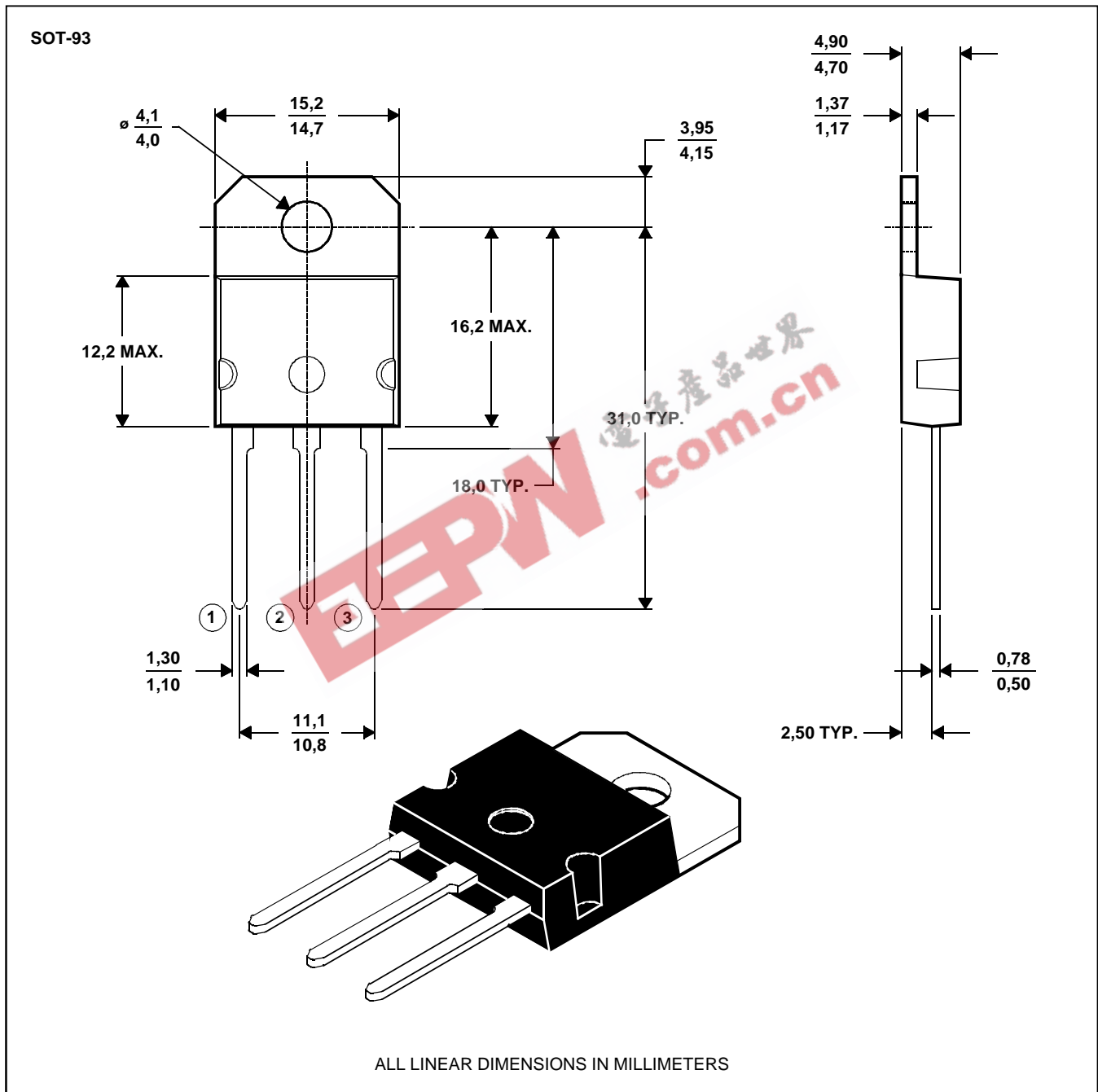
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## MECHANICAL DATA

### SOT-93

#### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

MDXXAW

## PRODUCT INFORMATION

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